



#### DMN601DWK

#### **DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

### **Product Summary**

| V <sub>(BR)DSS</sub> | R <sub>DS(ON)</sub> max   | I <sub>D</sub> max<br>T <sub>A</sub> = +25°C |
|----------------------|---------------------------|--|
| 60V                  | 3Ω @ V <sub>GS</sub> = 5V | 0.3A   |

### Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Motor Control
- Power Management Functions

#### **Features**

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

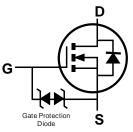
- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 leadframe (Lead-Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



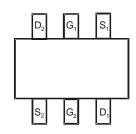


SOT363

Top View



Equivalent Circuit



Top View Internal Schematic

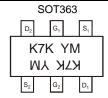
### **Ordering Information** (Note 4)

| Part Number | Case   | Packaging         |
|-------------|--------|-------------------|
| DMN601DWK-7 | SOT363 | 3,000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



K7K = Product Type Marking Code YM = Date Code Marking Y or Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

| Year  | 2005 | 2006 | 2007 | 2008 | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 | 2015 | 2016 | 2017 |
|-------|------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code  | S    | Т    | U    | V    | W    | Χ    | Υ    | Z    | Α    | В    | С    | D    | Е    |
| Month | Jan  | Feb  | Mar  | Apr  | Ma   | y Ju | ın . | Jul  | Aug  | Sep  | Oct  | Nov  | Dec  |
|       |      |      |      |      |      |      |      |      |      |      |      |      |      |



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic         | Symbol          | Value     | Unit |      |
|------------------------|-----------------|-----------|------|------|
| Drain Source Voltage   |                 | $V_{DSS}$ | 60   | V    |
| Gate-Source Voltage    |                 | $V_{GSS}$ | ±20  | V    |
| Drain Current (Note 5) | Continuous      | la .      | 305  | mA   |
| Diani Guitent (Note 3) | Pulsed (Note 6) | ID        | 800  | IIIA |

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                          | Symbol                            | Value       | Unit |
|---|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)        | P <sub>D</sub>                    | 200         | mW   |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$                   | 625         | °C/W |
| Operating and Storage Temperature Range | T <sub>J</sub> , T <sub>STG</sub> | -65 to +150 | °C   |

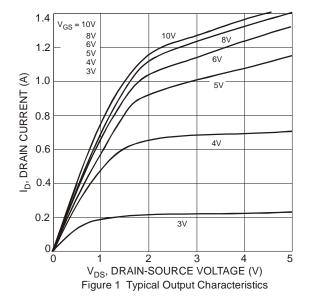
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

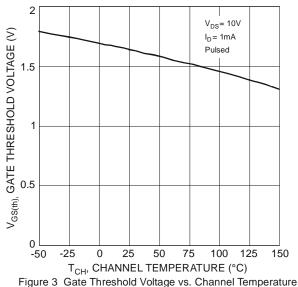
| Characteristic                    | Symbol                      | Min | Тур | Max        | Unit | Test Condition  |  |  |
|-----------------------------------|-----------------------------|-----|-----|------------|------|---|--|--|
| OFF CHARACTERISTICS (Note 7)      |                             |     |     |            |      |   |  |  |
| Drain-Source Breakdown Voltage    | BV <sub>DSS</sub>           | 60  |     |            | V    | $V_{GS} = 0V$ , $I_D = 10\mu A$                           |  |  |
| Zero Gate Voltage Drain Current   | I <sub>DSS</sub>            | _   |     | 1          | μΑ   | $V_{DS} = 60V, V_{GS} = 0V$                               |  |  |
| Gate-Source Leakage               | I <sub>GSS</sub>            | _   |     | ±10        | μΑ   | $V_{GS} = \pm 20V, V_{DS} = 0V$                           |  |  |
| ON CHARACTERISTICS (Note 7)       | ON CHARACTERISTICS (Note 7) |     |     |            |      |   |  |  |
| Gate Threshold Voltage            | V <sub>GS(th)</sub>         | 1.0 | 1.6 | 2.5        | ٧    | $V_{DS} = 10V$ , $I_D = 1mA$                              |  |  |
| Static Drain-Source On-Resistance | R <sub>DS(ON)</sub>         | _   |     | 2.0<br>3.0 | Ω    | $V_{GS} = 10V, I_D = 0.5A$<br>$V_{GS} = 5V, I_D = 0.05A$  |  |  |
| Forward Transfer Admittance       | Y <sub>fs</sub>             | 80  |     | _          | ms   | V <sub>DS</sub> =10V, I <sub>D</sub> = 0.2A               |  |  |
| Diode Forward Voltage<br>(Note 8) | V <sub>SD</sub>             | 0.5 | _   | 1.4        | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA              |  |  |
| DYNAMIC CHARACTERISTICS           |                             |     |     |            |      |   |  |  |
| Input Capacitance                 | C <sub>iss</sub>            | _   |     | 50         | рF   |   |  |  |
| Output Capacitance                | Coss                        | _   |     | 25         | рF   | V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V<br>f = 1.0MHz |  |  |
| Reverse Transfer Capacitance      | C <sub>rss</sub>            | _   |     | 5.0        | pF   | 1 - 1.00112   |  |  |

Notes:

- 5. Device mounted on FR-4 PCB.
- 6. Pulse width ≤10µS, Duty Cycle ≤1%.
  7. Short duration pulse test used to minimize self-heating effect.







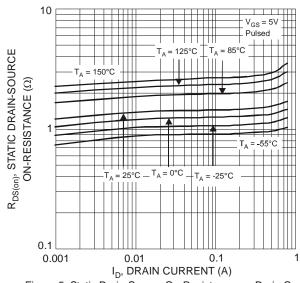
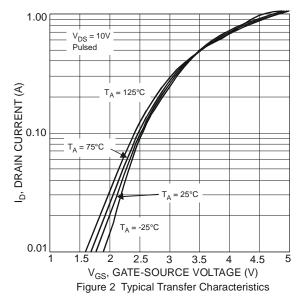


Figure 5 Static Drain-Source On-Resistance vs. Drain Current



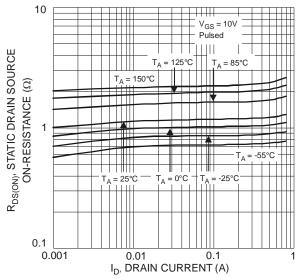


Figure 4 Static Drain-Source On-Resistance vs. Drain Current

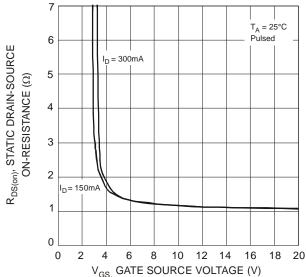
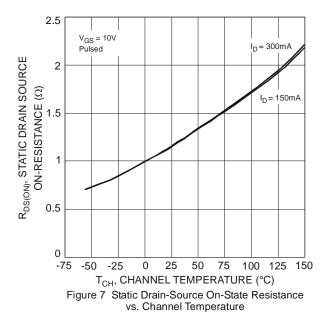


Figure 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage





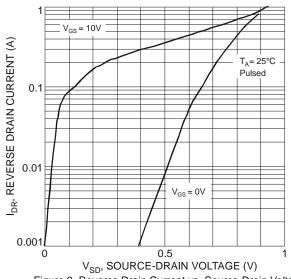
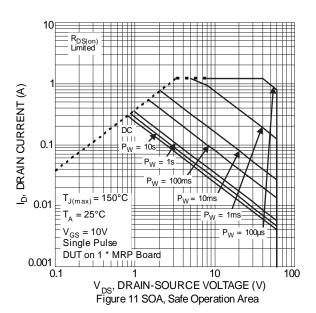


Figure 9 Reverse Drain Current vs. Source-Drain Voltage



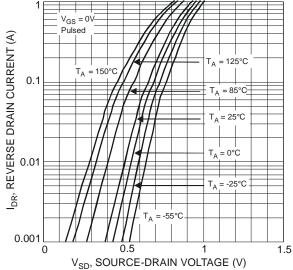


Figure 8 Reverse Drain Current vs. Source-Drain Voltage

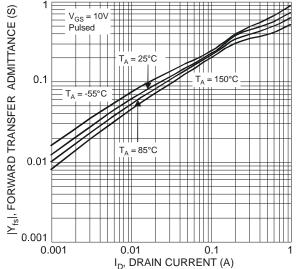
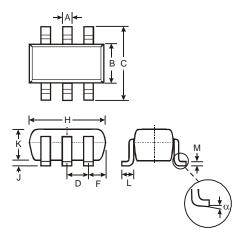


Figure 10 Forward Transfer Admittance vs. Drain Current



## **Package Outline Dimensions**

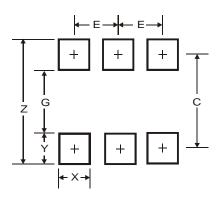
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



|                      | SOT363   |      |       |  |  |  |  |
|----------------------|----------|------|-------|--|--|--|--|
| Dim                  | Min      | Max  | Тур   |  |  |  |  |
| Α                    | 0.10     | 0.30 | 0.25  |  |  |  |  |
| В                    | 1.15     | 1.35 | 1.30  |  |  |  |  |
| ပ                    | 2.00     | 2.20 | 2.10  |  |  |  |  |
| D                    | 0.65 Typ |      |       |  |  |  |  |
| F                    | 0.40     | 0.45 | 0.425 |  |  |  |  |
| Н                    | 1.80     | 2.20 | 2.15  |  |  |  |  |
| 7                    | 0        | 0.10 | 0.05  |  |  |  |  |
| K                    | 0.90     | 1.00 | 1.00  |  |  |  |  |
| L                    | 0.25     | 0.40 | 0.30  |  |  |  |  |
| М                    | 0.10     | 0.22 | 0.11  |  |  |  |  |
| α                    | 0°       | 8°   | -     |  |  |  |  |
| All Dimensions in mm |          |      |       |  |  |  |  |

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.5           |
| G          | 1.3           |
| Х          | 0.42          |
| Y          | 0.6           |
| С          | 1.9           |
| F          | 0.65          |



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